



FIG. 1

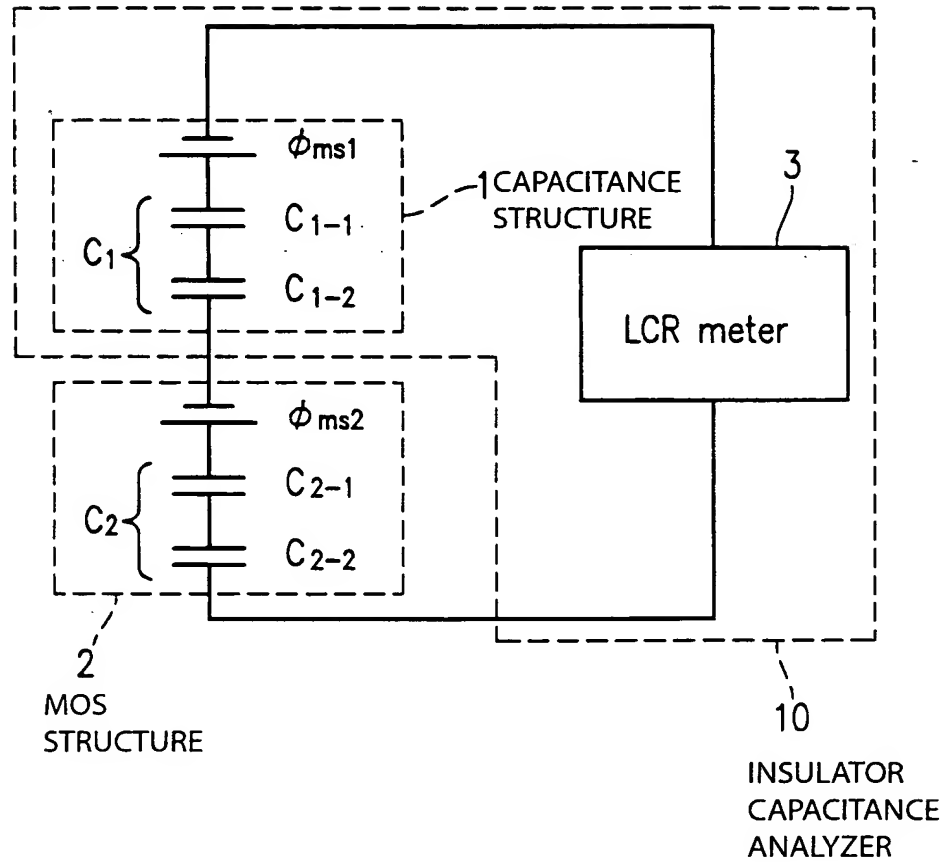




FIG. 2

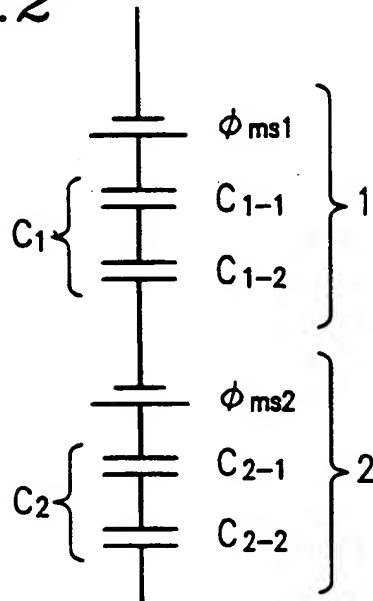
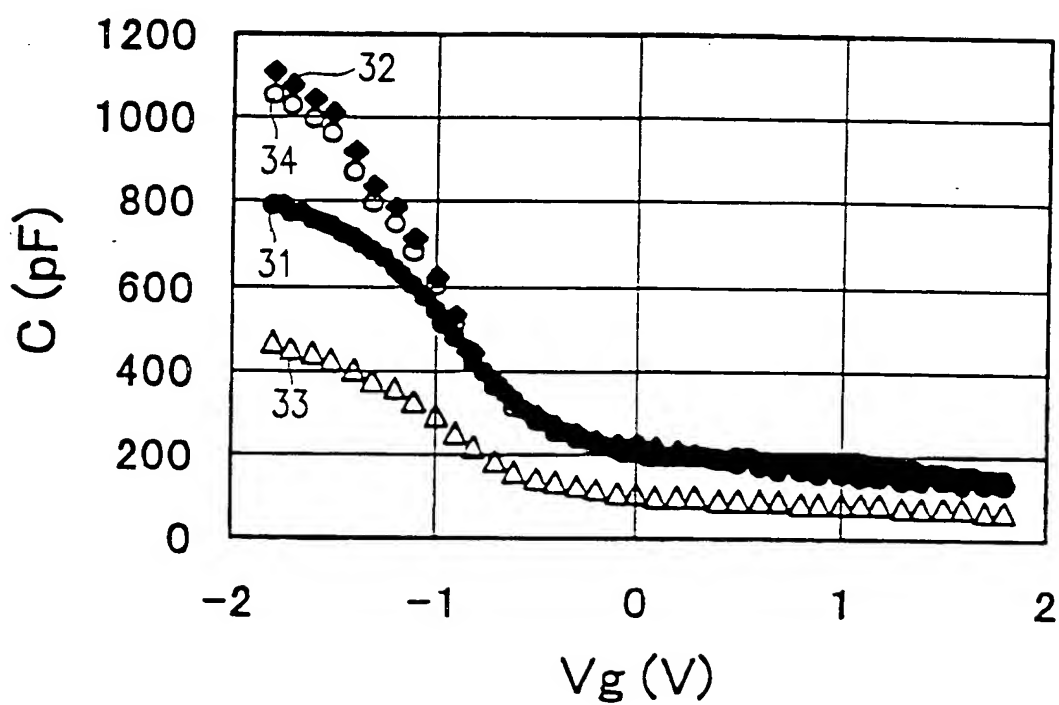




FIG. 3

NMOS C-V Characteristics



- 3.2nmC-V measured curve
- ◆— 2nmC-V ideal curve
- △— Synthesis curve
- 2nmC-V conversion curve



FIG. 4

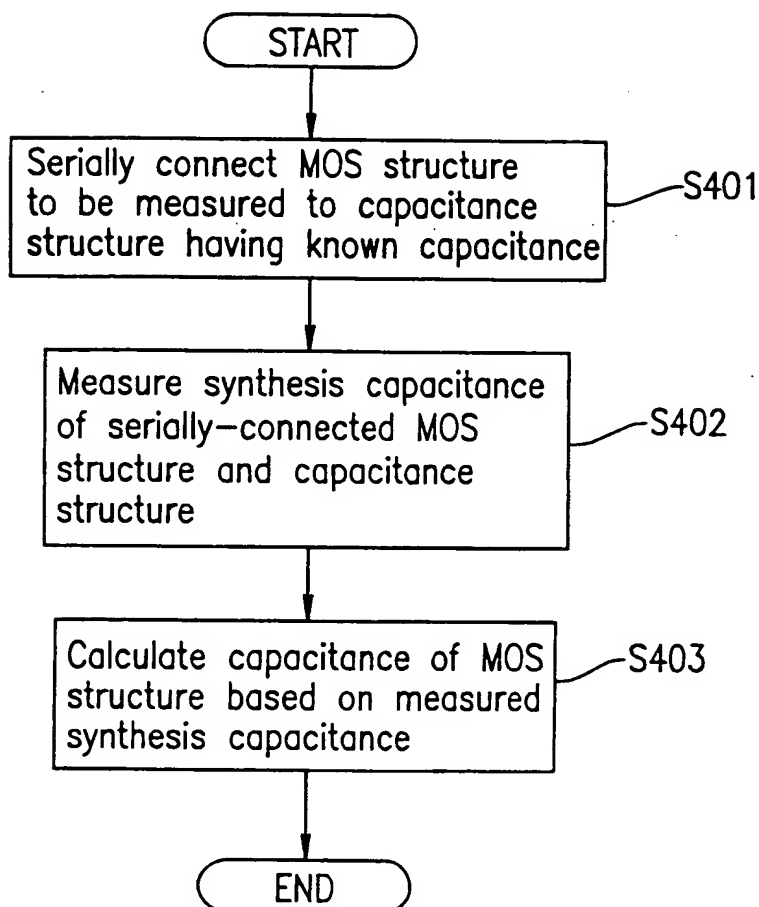




FIG. 5

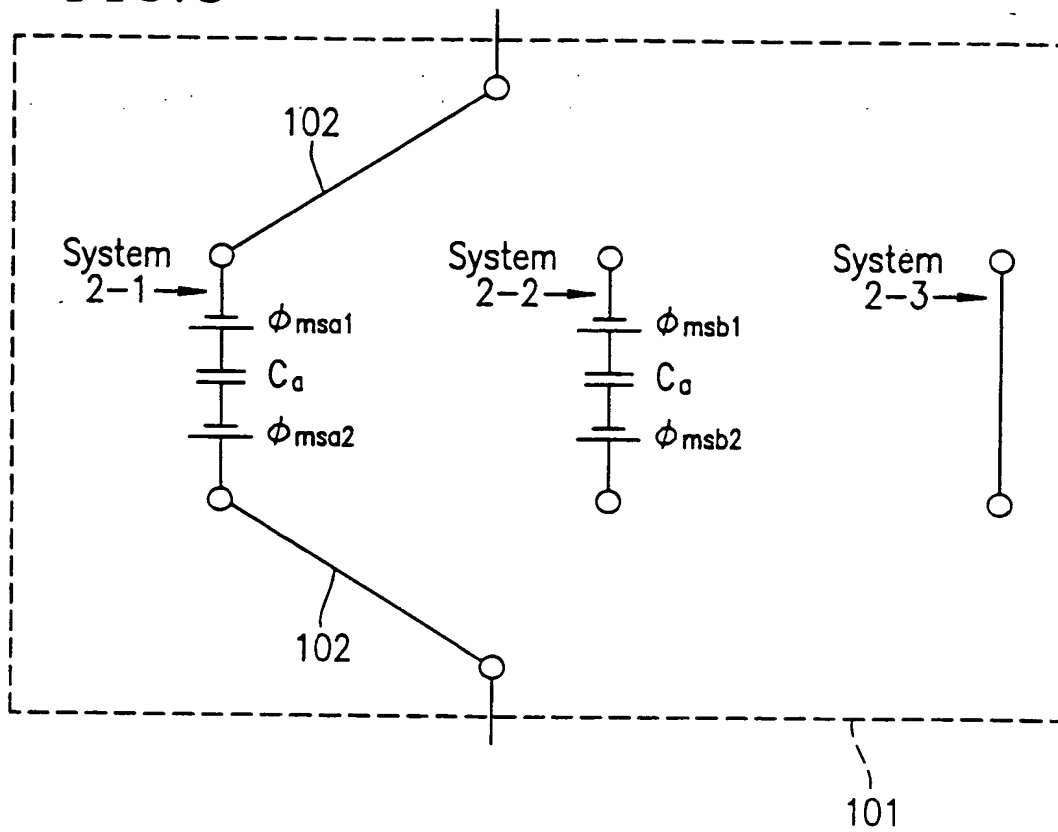
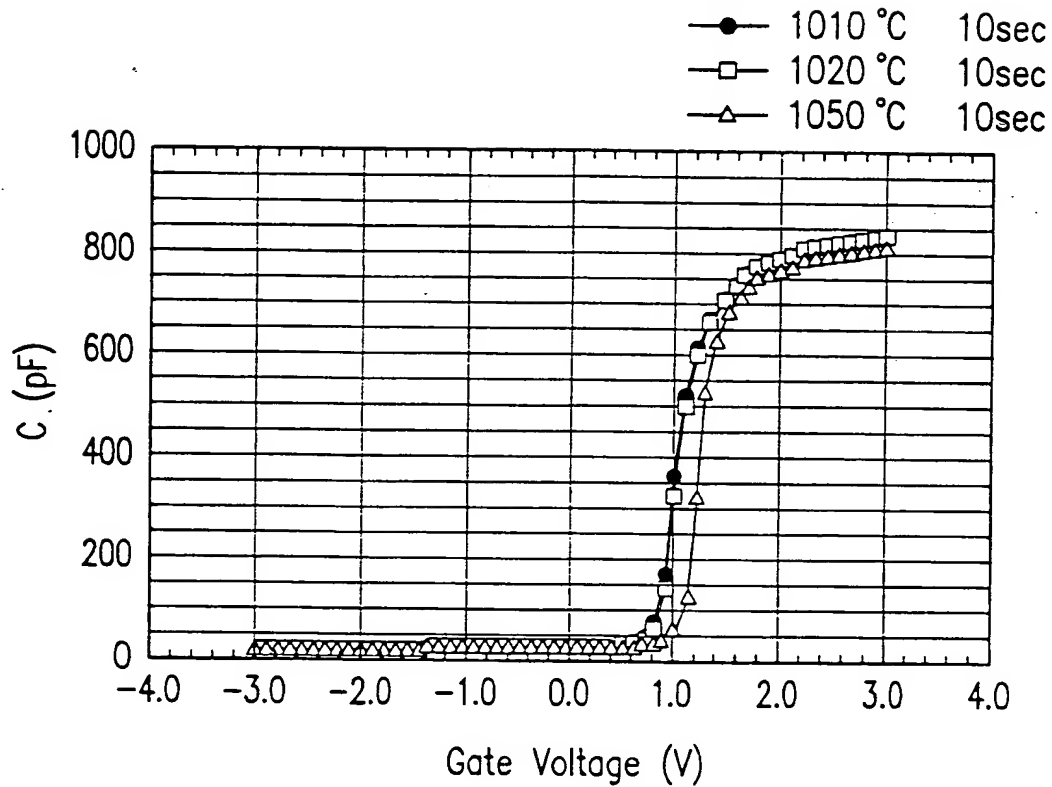




FIG. 6

PMOS C-V Characteristics



Active Area: $9\text{E}-4\text{cm}^2$

w/o Well Imp.

Gate SiON: NO/N₂

poly Si: 200nm

P+Imp.: BF₂



FIG. 7

NMOS I-V Characteristics

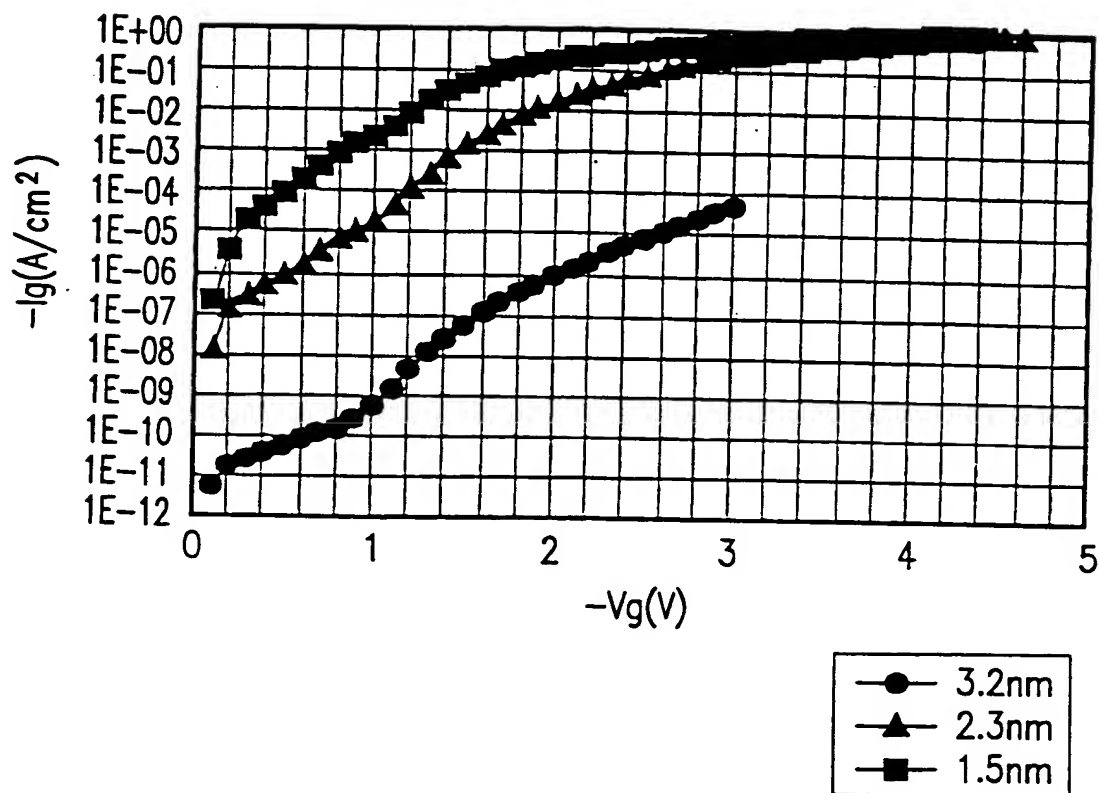
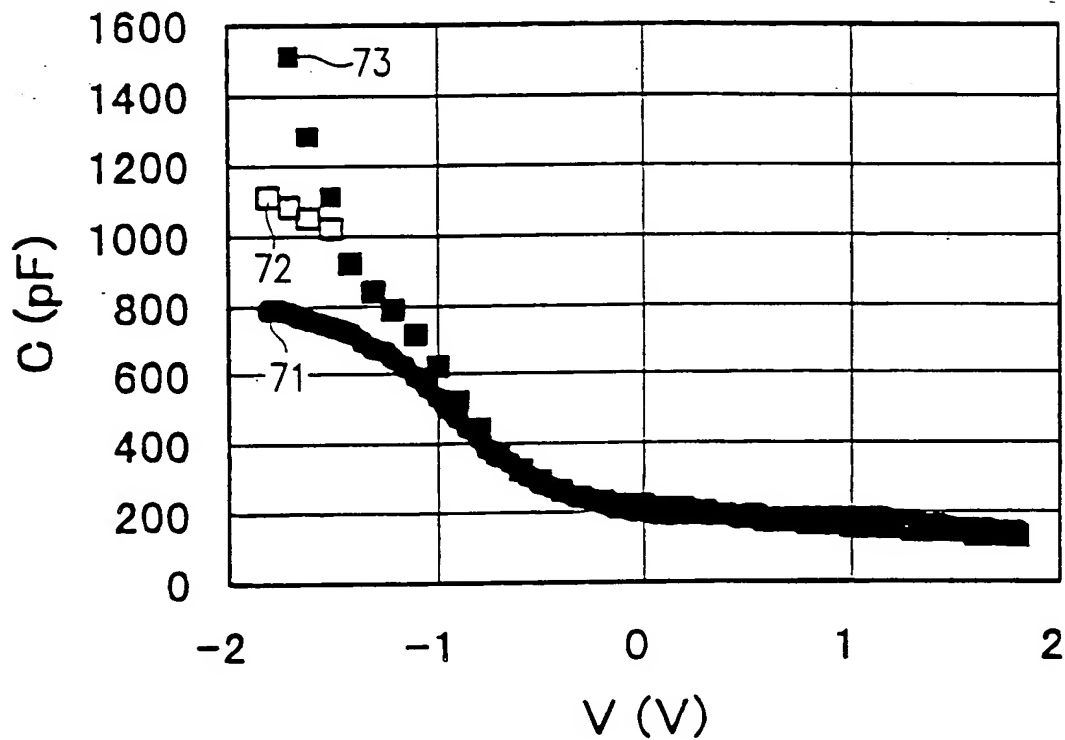




FIG. 8

NMOS C-V Characteristics



- 3.2nmC-V measured curve
- 2nmC-V ideal curve
- 2nmC-V measured curve



FIG. 9

